

P-Channel 12-V (D-S) MOSFET

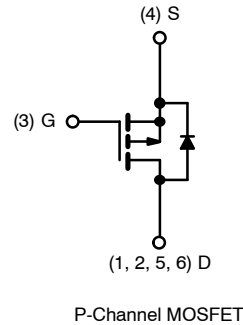
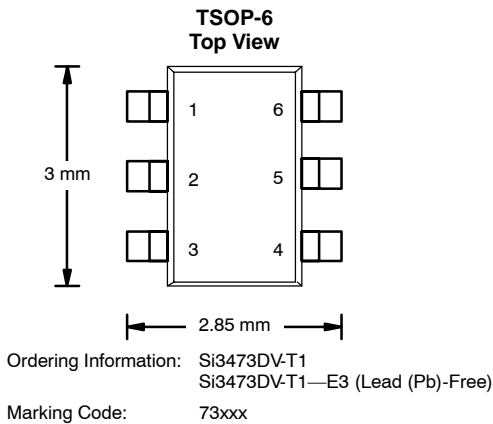
PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
-12	0.023 @ $V_{GS} = -4.5$ V	-7.9	22
	0.029 @ $V_{GS} = -2.5$ V	-7.0	
	0.041 @ $V_{GS} = -1.8$ V	-5.9	

FEATURES

- TrenchFET® Power MOSFET: 1.8-V Rated
- Ultra Low On-Resistance

APPLICATIONS

- Load Switch
- PA Switch



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-12		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-7.9	-5.9	A
		$T_A = 85^\circ\text{C}$	-5.7	-4.3	
Pulsed Drain Current	I_{DM}	-20			
Continuous Diode Current (Diode Conduction) ^a	I_S	-1.7	-0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	2.0	1.1	W
		$T_A = 85^\circ\text{C}$	1.0	0.6	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	45	62.5	$^\circ\text{C/W}$
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.



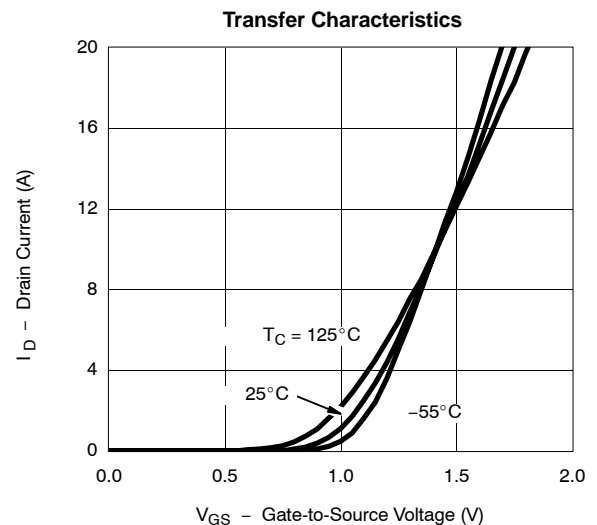
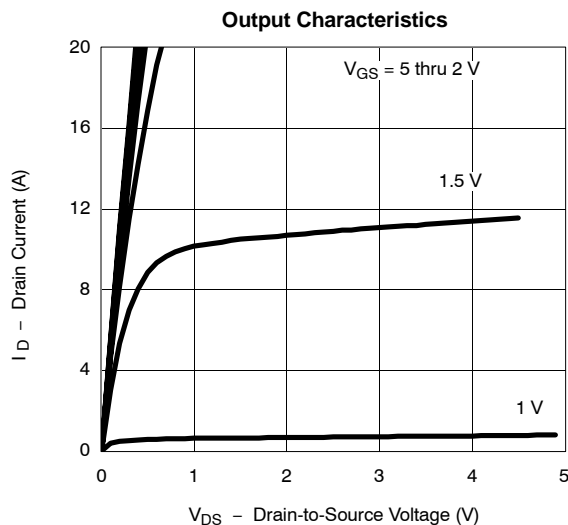
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.40		-1	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -12 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -4.5 V	-20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -7.9 A		0.019	0.023	Ω
		V _{GS} = -2.5 V, I _D = -7.0 A		0.024	0.029	
		V _{GS} = -1.8 V, I _D = -3 A		0.033	0.041	
Forward Transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -7.9 A		28		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1.7 A, V _{GS} = 0 V		-0.7	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -6 V, V _{GS} = -4.5 V, I _D = -7.9 A		22	33	nC
Gate-Source Charge	Q _{gs}			3.2		
Gate-Drain Charge	Q _{gd}			5.8		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6 V, R _L = 6 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _g = 6 Ω		25	40	ns
Rise Time	t _r			50	75	
Turn-Off Delay Time	t _{d(off)}			130	200	
Fall Time	t _f			110	165	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -1.7 A, di/dt = 100 A/μs		65	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

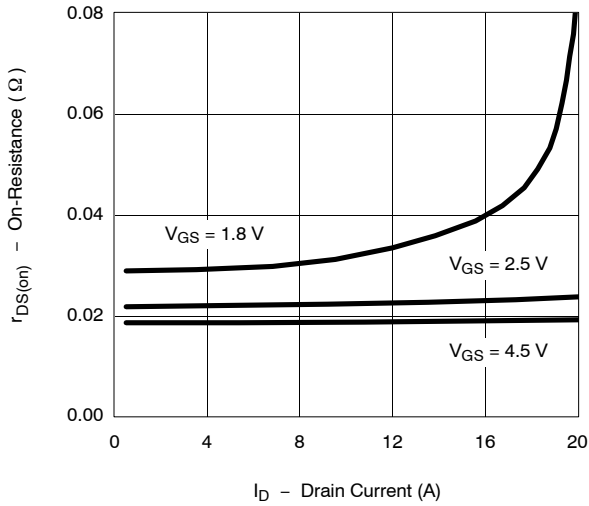
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



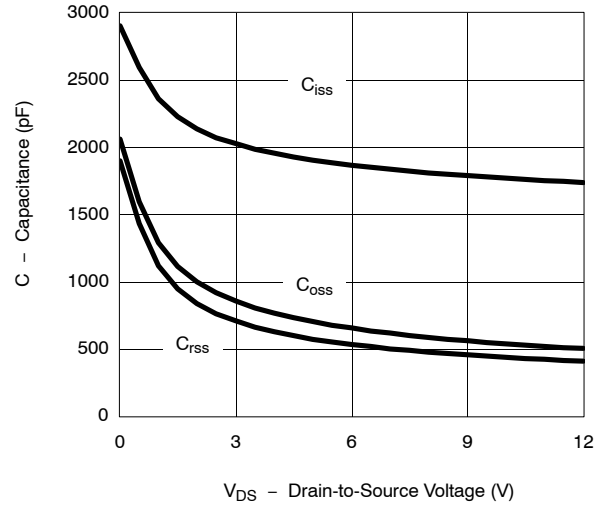


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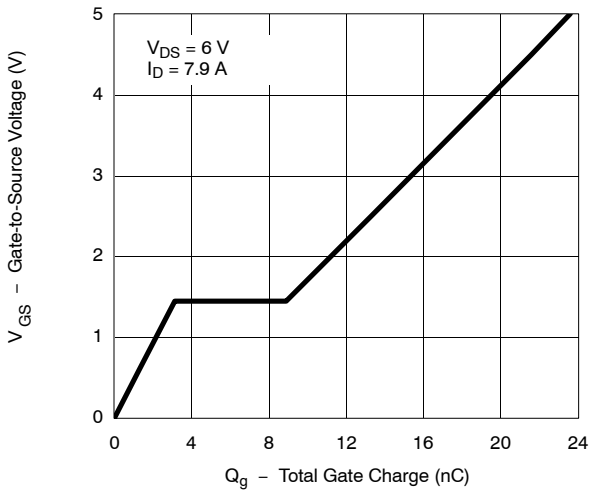
On-Resistance vs. Drain Current



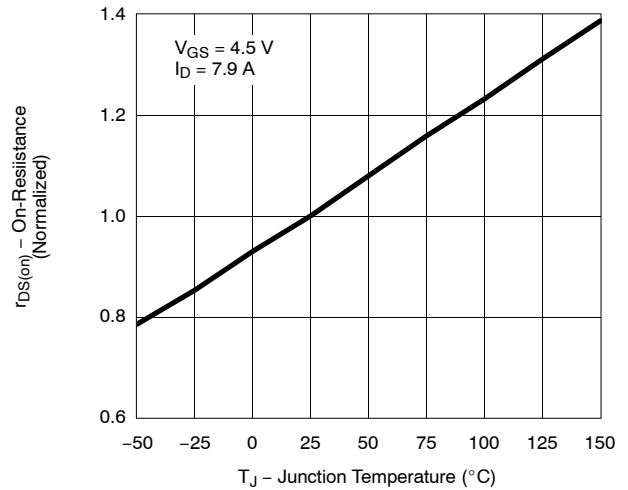
Capacitance



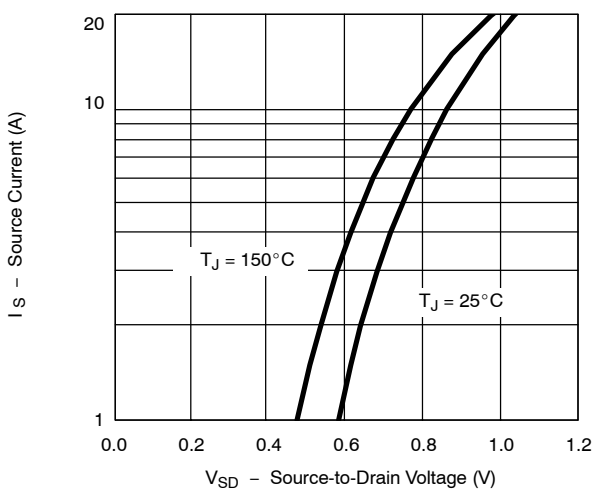
Gate Charge



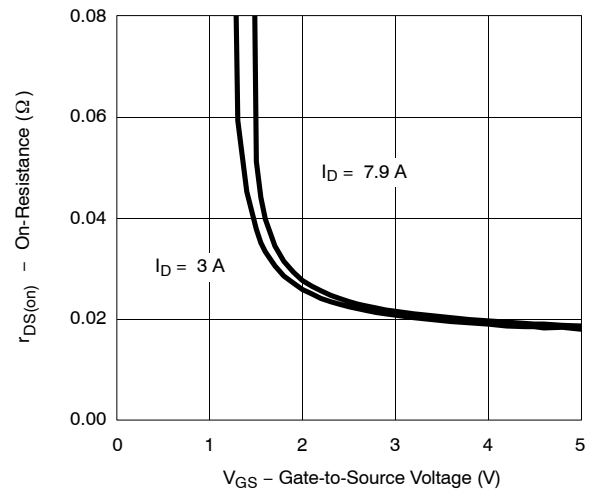
On-Resistance vs. Junction Temperature



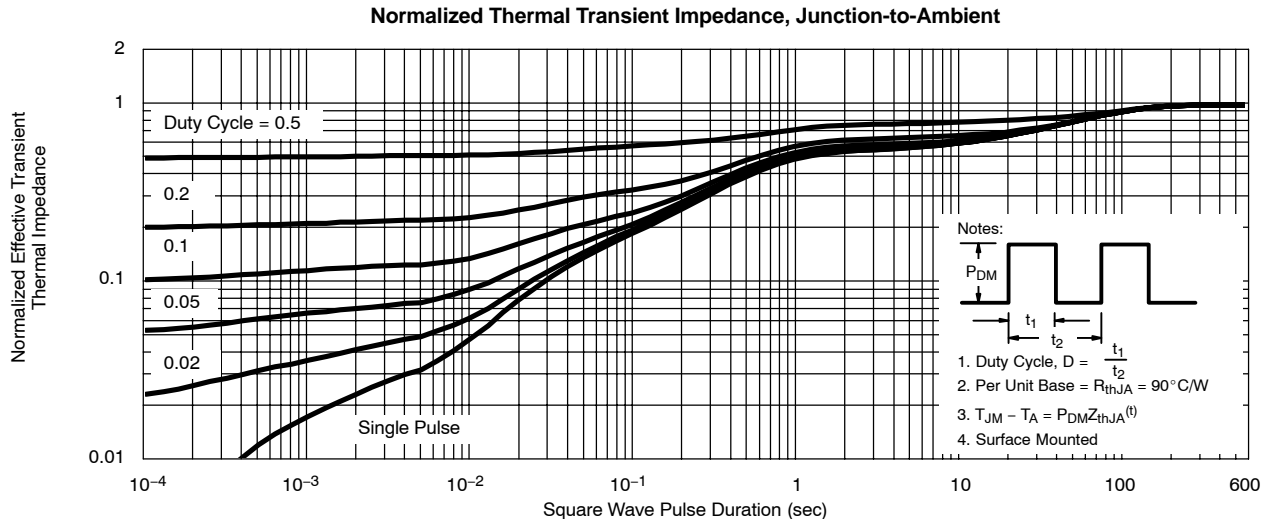
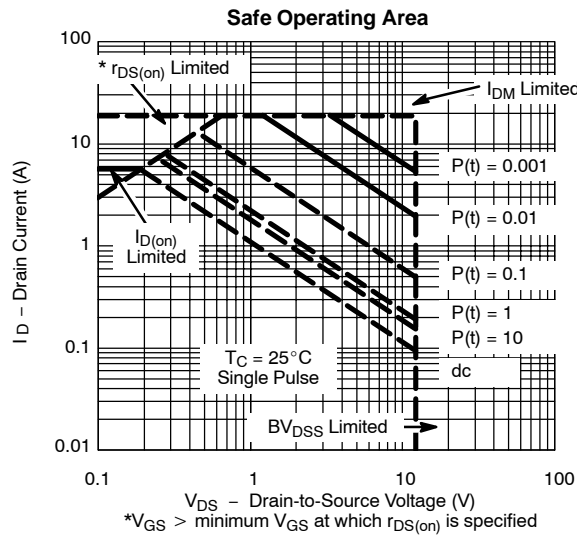
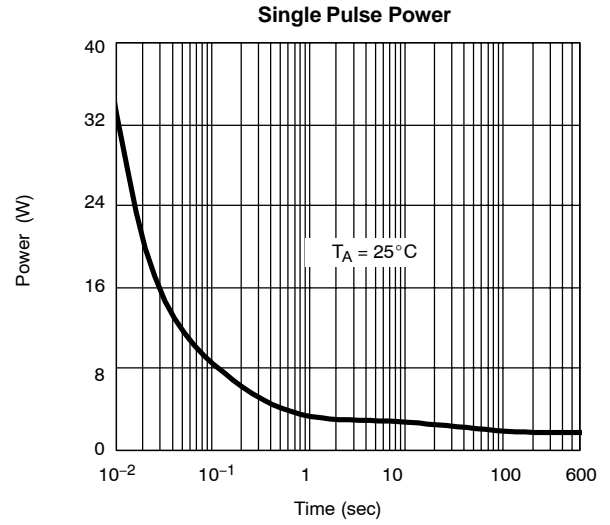
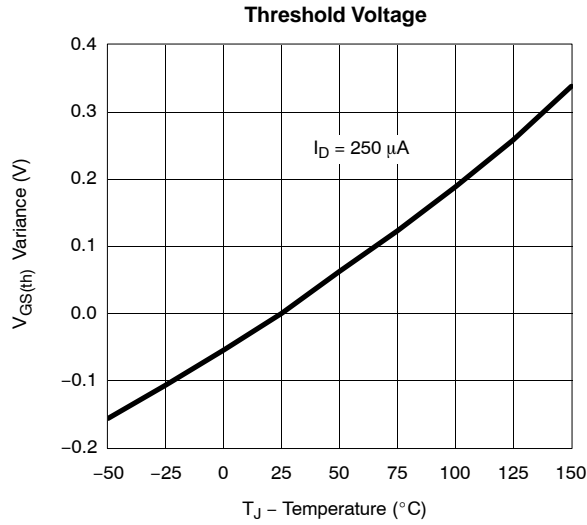
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

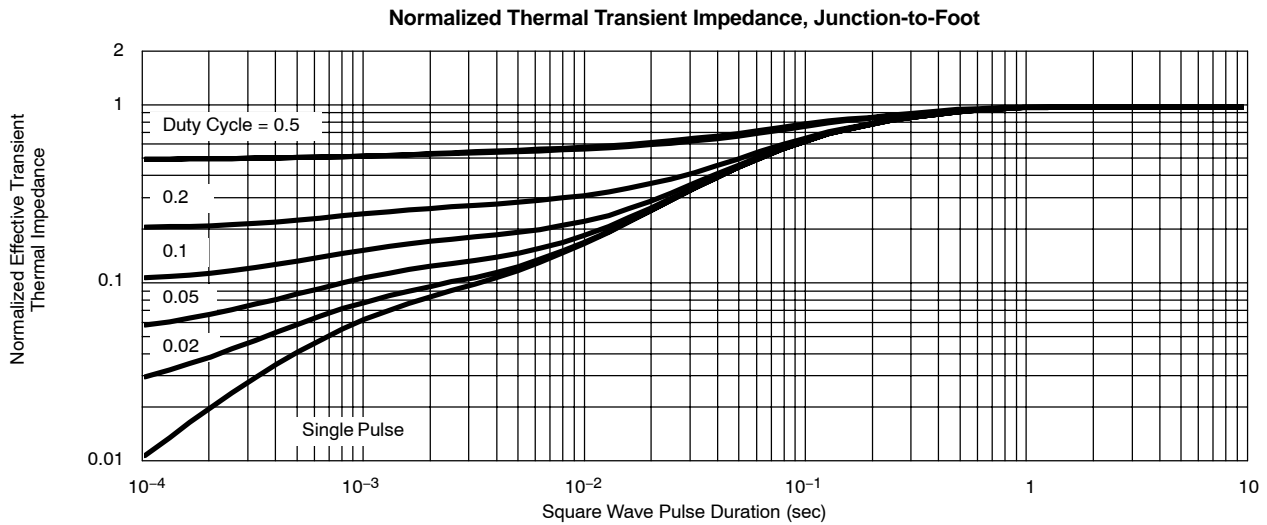


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